

## **Preliminary**

# **TSM4835**

### 30V P-Channel MOSFET

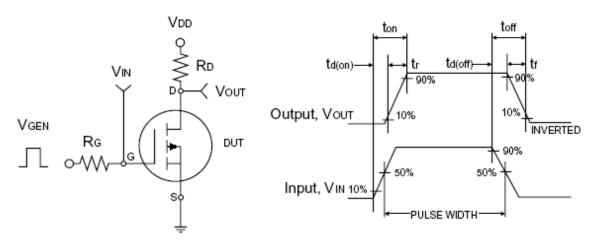


**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit		
Static								
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV <sub>DSS</sub>	-30	I		V		
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1	I	-3	V		
Gate Body Leakage	$V_{GS} = \pm 25V, V_{DS} = 0V$	$I_{GSS}$		1	±100	nA		
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I <sub>DSS</sub>			-1.0	μA		
On-State Drain Current <sup>a</sup>	V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> = -10V	I <sub>D(ON)</sub>	-50			Α		
Dunin Course On State Desistance	$V_{GS} = -10V, I_D = -9.6A$	0		14	18	mΩ		
Drain-Source On-State Resistance <sup>a</sup>	$V_{GS} = -4.5V, I_D = -7.5A$	$R_{DS(ON)}$		23	30			
Forward Transconductance <sup>a</sup>	$V_{DS} = -15V, I_{D} = -9.6A$	g <sub>fs</sub>		30		S		
Diode Forward Voltage	I <sub>S</sub> = -2.1A, V <sub>GS</sub> = 0V	$V_{SD}$		-0.8	-1.2	V		
Dynamic <sup>b</sup>								
Total Gate Charge	$V_{DS} = -15V, I_{D} = -9.6A,$ $V_{GS} = -5V$	$Q_g$		25	37	nC		
Gate-Source Charge		$Q_gs$		6.5				
Gate-Drain Charge	V <sub>GS</sub> = -5 V	$Q_{gd}$		12.5				
Input Capacitance	\/ - 15\/ \/ - 0\/	$C_{iss}$		2089	2347	pF		
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		597				
Reverse Transfer Capacitance	1 - 1.000112	$C_{rss}$		495	624			
Switching <sup>c</sup>								
Turn-On Delay Time	$V_{DD} = -15V, R_L = 15\Omega,$	t <sub>d(on)</sub>		15	25	nS		
Turn-On Rise Time		t <sub>r</sub>		13	20			
Turn-Off Delay Time	$I_D = -1A$ , $V_{GEN} = -10V$ , $R_G = 6Ω$	$t_{d(off)}$		60	100			
Turn-Off Fall Time	1/C - 075	t <sub>f</sub>		45	70			

#### Notes:

- a. pulse test: PW  $\leq 300 \mu S$ , duty cycle  $\leq 2\%$  b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

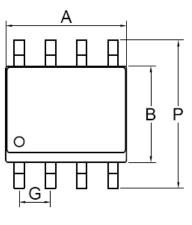


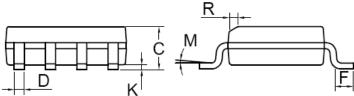
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# **SOP-8 Mechanical Drawing**





SOP-8 DIMENSION							
DIM	MILLIMETERS		INCHES				
	MIN	MAX	MIN	MAX.			
Α	4.80	5.00	0.189	0.196			
В	3.80	4.00	0.150	0.157			
С	1.35	1.75	0.054	0.068			
D	0.35	0.49	0.014	0.019			
F	0.40	1.25	0.016	0.049			
G	1.27	BSC	0.05	0.05BSC			
K	0.10	0.25	0.004	0.009			
М	0°	7°	0°	7°			
Р	5.80	6.20	0.229	0.244			
R	0.25	0.50	0.010	0.019			



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4/4 Version: Preliminary